# 40V P-Channel Trench Power MOSFET

## General Description

The SJH40PD085 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.

## Features

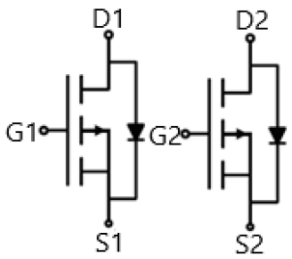
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handing capability
- Lead free product is acquired

## Application

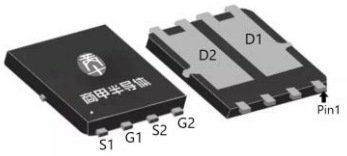
- PWM Applications
- Load Switch
- Power Management

## Key Performance Parametes

| Parameter | Value | Unit |
|---|---|---|
| $V_{DS}$ | -40 | V |
| $R_{DS(ON)\_TYP}$ | 10.9 | mΩ |
| $I_D$ | -45 | A |
| $Q_G$ | 60 | nC |




Schematic Diagram




PDFN5X6-8L top&bottom view

RoHS

## Package Marking and Ordering Information

| Device/Ordering Code | Marking | Package | Packing | Reel Size | Tape width | Quantity |
|---|---|---|---|---|---|---|
| SJH40PD085 | SJH40PD085 | PDFN5X6-8L | Tape | \ | \ | 5000 Pcs |

## Table 1. Absolute Maximum Ratings ($T_C$=25℃ unless otherwise noted)

| Symbol | Parameter | Limit | Unit |
|---|---|---|---|
| $V_{DS}$ | Drain-Source Voltage ($V_{GS}$=0V) | -40 | V |
| $V_{GS}$ | Gate-Source Voltage ($V_{DS}$=0V) | ±20 | V |
| $I_D$ | Drain Current-Continuous($T_C$=25℃) | -45 | A |
| | Drain Current-Continuous($T_C$=100℃) | -28 | A |
| $I_{DM\ (pluse)}$ | Drain Current-Continuous@ Current-Pulsed (Note 1) | -180 | A |
| $P_D$ | Maximum Power Dissipation($T_C$=25℃) | 50 | W |
| | Maximum Power Dissipation($T_C$=100℃) | 20 | W |
| $E_{AS}$ | Avalanche energy (Note 2) | 272 | mJ |
| $T_J$, $T_{STG}$ | Operating Junction and Storage Temperature Range | -55 To 150 | ℃ |

## Table 2. Thermal Characteristic

| Symbol | Parameter | Typ | Max | Unit |
|---|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | | 2.48 | ℃/W |

## Table 3. Electrical Characteristics ($T_J$=25℃ unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **On/Off States** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}$=0V $I_D$=-250μA | -40 | | | V |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$=-40V, $V_{GS}$=0V $T_J$=25℃ | | | -1 | μA |
| | | $V_{DS}$=-40V, $V_{GS}$=0V $T_J$=125℃ | | | -100 | μA |
| $I_{GSS}$ | Gate-Body Leakage Current | $V_{GS}$=±20V, $V_{DS}$=0V | | | ±100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$=$V_{GS}$, $I_D$=-250μA | -1 | | -2.5 | V |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$=-5V, $I_D$=-10A | | 31 | | S |
| $R_{DS(ON)}$ | Drain-Source On-State Resistance | $V_{GS}$=-10V, $I_D$=-20A $T_J$=25℃ | | 10.9 | 14.2 | mΩ |
| $R_{DS(ON)}$ | Drain-Source On-State Resistance | $V_{GS}$=-4.5V, $I_D$=-20A $T_J$=25℃ | | 14.5 | 19.3 | mΩ |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$=-20V,$V_{GS}$=0V, f=1.0MHz | | 3241 | | pF |
| $C_{oss}$ | Output Capacitance | | | 228 | | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 205 | | pF |
| $R_g$ | Gate resistance | $V_{GS}$=0V, $V_{DS}$=0V, f=1.0MHz | | 4.5 | | Ω |
| **Switching Parameters** | | | | | | |
| $t_{d(on)}$ | Turn-on Delay Time | $V_{GS}$=-10V, $V_{DS}$=-20V, $R_L$=1Ω, $R_{GEN}$=3Ω | | 18 | | nS |
| $t_r$ | Turn-on Rise Time | | | 4.8 | | nS |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 88.8 | | nS |
| $t_f$ | Turn-Off Fall Time | | | 26.4 | | nS |
| $Q_g$ | Total Gate Charge | $V_{GS}$=-10V, $V_{DS}$=-20V, $I_D$=-20A | | 60 | | nC |
| $Q_{gs}$ | Gate-Source Charge | | | 8.6 | | nC |
| $Q_{gd}$ | Gate-Drain Charge | | | 13.9 | | nC |
| **Source-Drain Diode Characteristics** | | | | | | |
| $I_{SD}$ | Source-Drain Current (Body Diode) | | | | -45 | A |
| $V_{SD}$ | Forward on Voltage (Note 3) | $V_{GS}$=0V, $I_S$=-10A | | | -1.2 | V |
| $t_{rr}$ | Reverse Recovery Time | $I_F$=-10A, dI/dt=-100A/μs | | 17.3 | | ns |
| $Q_{rr}$ | Reverse Recovery Charge | $I_F$=-10A, dI/dt=-100A/μs | | 9.5 | | nC |

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.$E_{AS}$ condition: $T_J$=25℃,$V_{DD}$=-40V,$V_G$=-10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

## Typical Electrical And Thermal Characteristics (Curves)

**Figure 1. Output Characteristics**

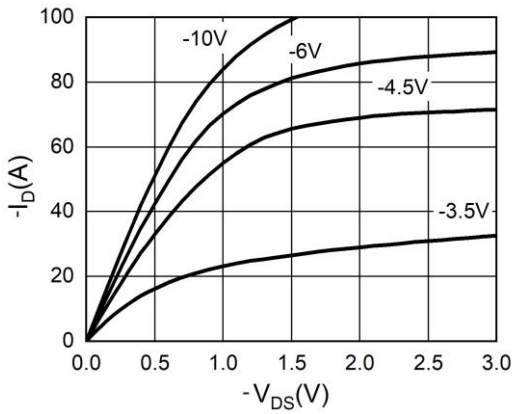



**Figure 2. Transfer Characteristics**

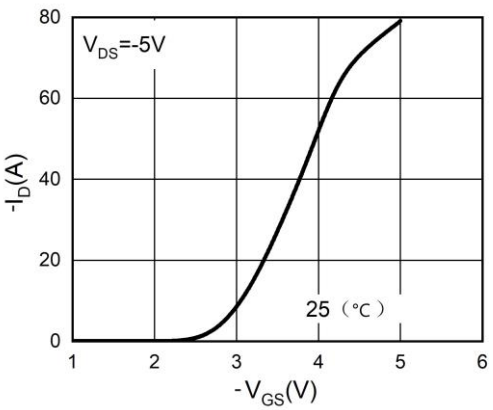



**Figure 3. Power Dissipation**

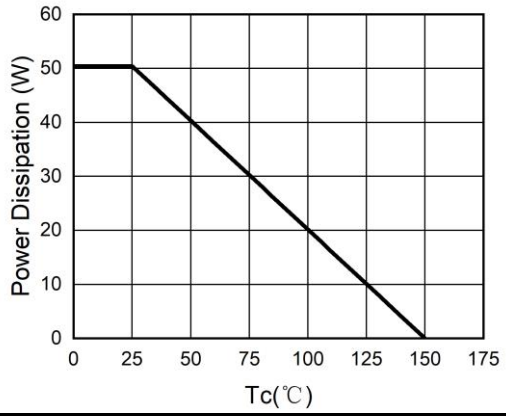



**Figure 4. Drain Current**

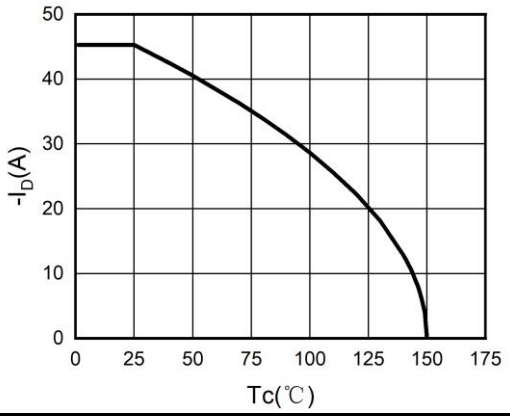



**Figure 5. $BV_{DSS}$ vs Junction Temperature**

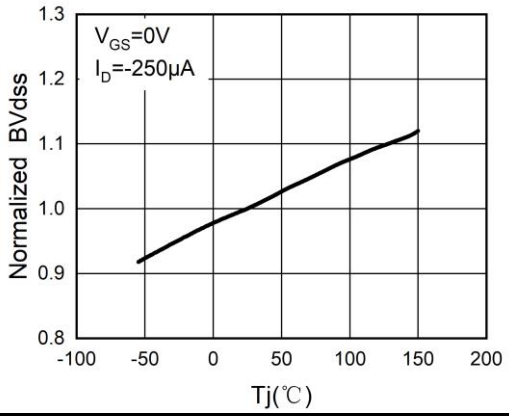
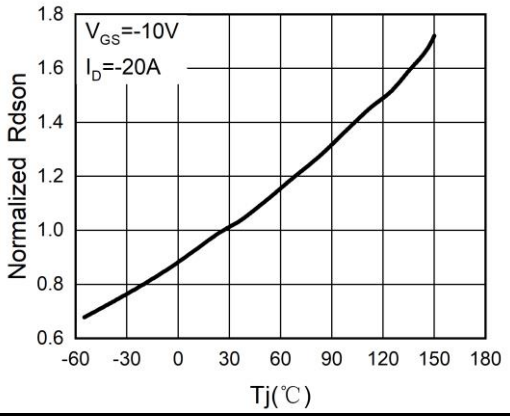



**Figure 6. $R_{DS(ON)}$ vs Junction Temperature**



## Typical Electrical And Thermal Characteristics (Curves)

**Figure 7. Gate Charge Waveforms**

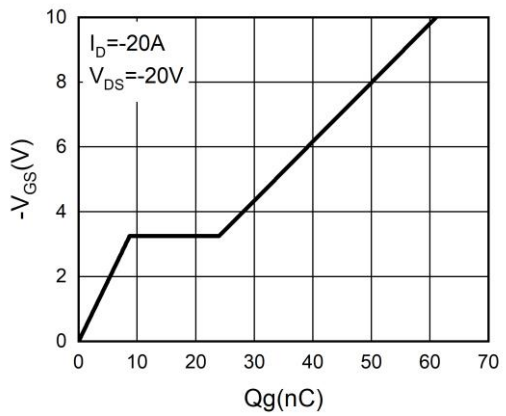



**Figure 8. Capacitance**

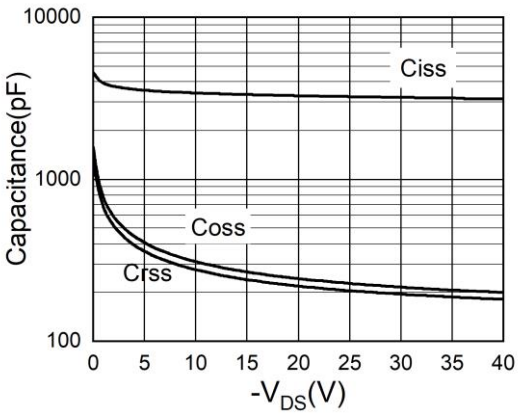



**Figure 9. Body-Diode Characteristics**

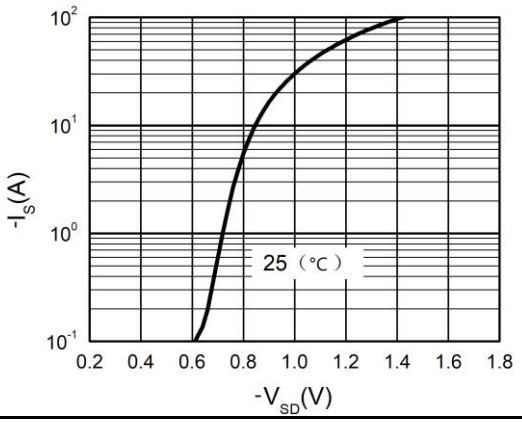
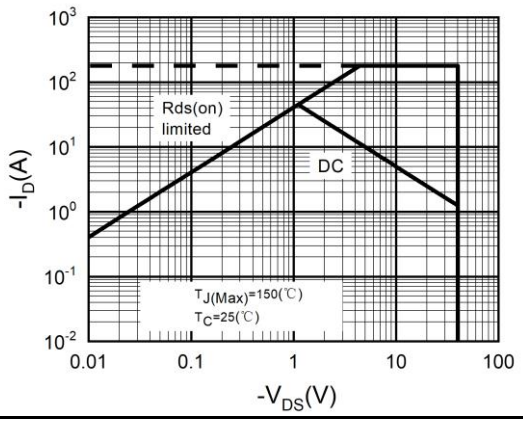
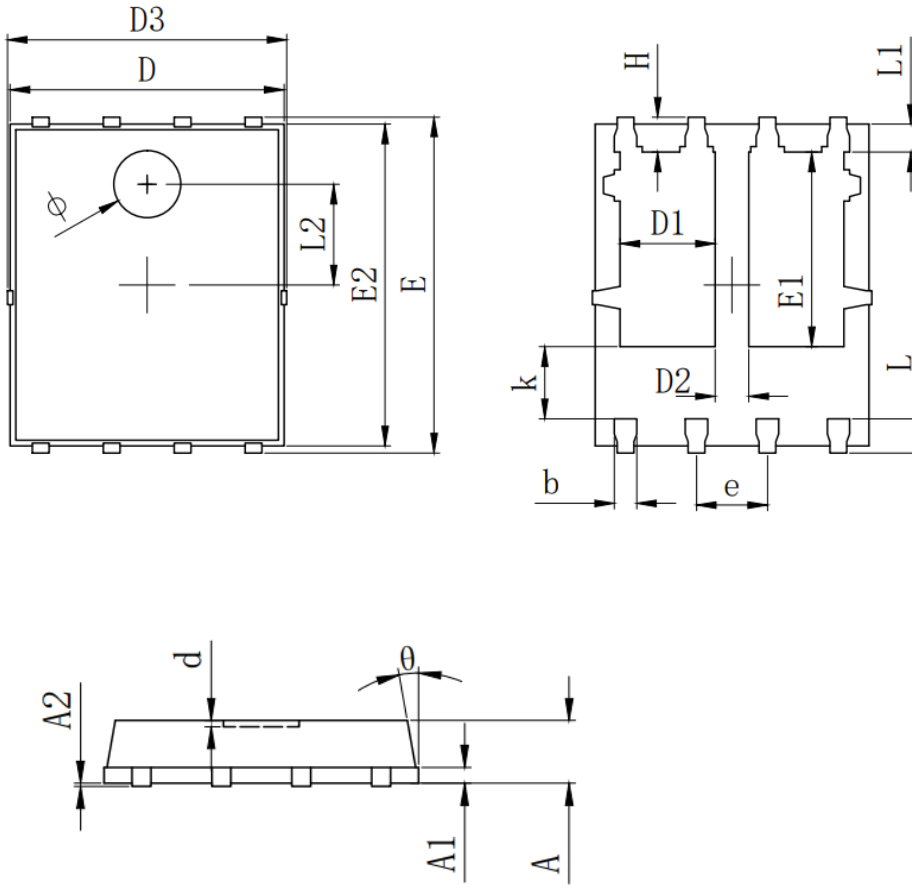



**Figure 10. Maximum Safe Operating Area**



## PDFN5X6 Package Information




| SYMBOL | MILLIMETER | | |
|---|---|---|---|
| | MIN | Typ. | MAX |
| A | 0.900 | 1.000 | 1.100 |
| A1 | 0.254 REF. | | |
| A2 | 0~0.05 | | |
| D | 4.824 | 4.900 | 4.976 |
| D1 | 1.605 | 1.705 | 1.805 |
| D2 | 0.500 | 0.600 | 0.700 |
| D3 | 4.924 | 5.000 | 5.076 |
| E | 5.924 | 6.000 | 6.076 |
| E1 | 3.375 | 3.475 | 3.575 |
| E2 | 5.674 | 5.750 | 5.826 |
| b | 0.350 | 0.400 | 0.450 |
| e | 1.270 TYP. | | |
| L | 0.534 | 0.610 | 0.686 |
| L1 | 0.424 | 0.500 | 0.576 |
| L2 | 1.800 REF. | | |
| k | 1.190 | 1.290 | 1.390 |
| H | 0.549 | 0.625 | 0.701 |
| θ | 8° | 10° | 12° |
| Φ | 1.100 | 1.200 | 1.300 |
| d | | | 0.100 |

| **Symbol** | MILLIMETER | | |
|---|---|---|---|
| | **Min.** | **Typ.** | **Max.** |
| A | 0.900 | 1.000 | 1.100 |
| A1 | 0.254 REF. | | |
| A2 | 0~0.05 | | |
| D | 4.824 | 4.900 | 4.976 |
| D1 | 3.910 | 4.010 | 4.110 |
| D2 | 4.924 | 5.000 | 5.076 |
| E | 5.924 | 6.000 | 6.076 |
| E1 | 3.375 | 3.475 | 3.575 |
| E2 | 5.674 | 5.75 | 5.826 |
| b | 0.350 | 0.400 | 0.450 |
| e | 1.270 TYP. | | |
| L | 0.534 | 0.610 | 0.686 |
| L1 | 0.424 | 0.500 | 0.576 |
| L2 | 1.800 REF. | | |
| k | 1.190 | 1.290 | 1.390 |
| H | 0.549 | 0.625 | 0.701 |
| θ | 8° | 10° | 12° |
| Φ | 1.100 | 1.200 | 1.300 |
| d | | | 0.100 |

## Attention

This product described in this document can not be used in life support devices or systems, aircraft's control systems, and other applications whose failure can be reasonably expected to result in serious physical and/or material damage，apart from that when an application agreement is signed between customer and Wuxi Shangjia Semiconductor.

The performances and characteristics of this product in the independent testing state are displayed in this document. Wuxi Shangjia Semiconductor can't guarantee of the performances and characteristics of this described product that mounted in the customer's products or equipments as same as that in the independent testing state. So the customer should evaluate and test devices mounted in the customer's products or equipments.

Wuxi Shangjia Semiconductor reserves the right to improve the designs, functions and reliability of this product and modify any and all information described in this document without notice customer, apart from that when an notice agreement is signed between customer and Wuxi Shangjia Semiconductor.

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Wuxi Shangjia Semiconductor hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.